

KEY FEATURES

- Ideal for extremely low noise cryogenic applications
- Powered from a single positive DC supply
- Female SMA RF connectors
- 2-pin winchester DC connectors
- Optional DC bias tees
- Size 2.07 cm x 1.59 cm x 0.87 cm

PERFORMANCE FEATURES

- RF Frequency
 - o 0.01 to 1.5 GHz
- Gain
 - $33 dB \pm 3 dB$
- Noise Temperature
 - o < 4 K
- Noise Figure
 - o < 0.06 dB
- Optimum DC Power
 - o Vd = 1.8 V
 - \circ Id = 8.9 mA



Cryogenic SiGe Low Noise Amplifie



Description

- ➤ The CITLF2, a SiGe low noise amplifier, is intended for extremely low noise cryogenic applications. The amplifier uses resistive feedback to achieve good input match (S11) and high gain stability. The amplifier is optimum for the frequency range of 0.01 GHz to 1.5 GHz. High gain and low noise is also achieved up to 5 GHz.
- ➤ It is powered from a single positive DC power supply which is optimum at 1.8 V, but can be reduced to as low as 1.1 V for low power dissipation. Application of up to 5 V will not damage the amplifier. It is recommended that the power supply for the amplifier to be current limited to 100 mA.
- ➤ The amplifier is 20.7 mm x 15.9 mm x 8.7 mm excluding connectors. Input and output female SMA connectors.

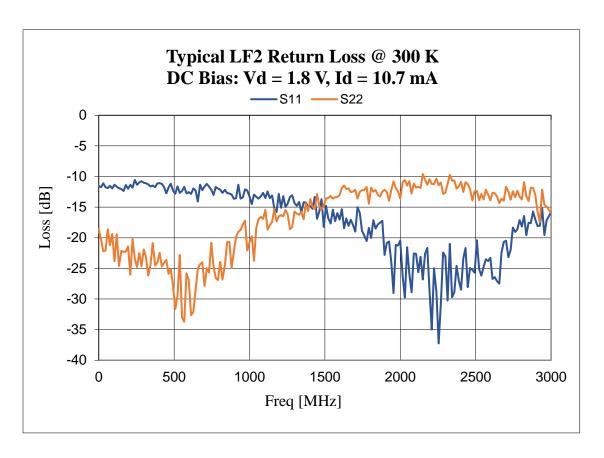
Electrical Specifications @ 12 K

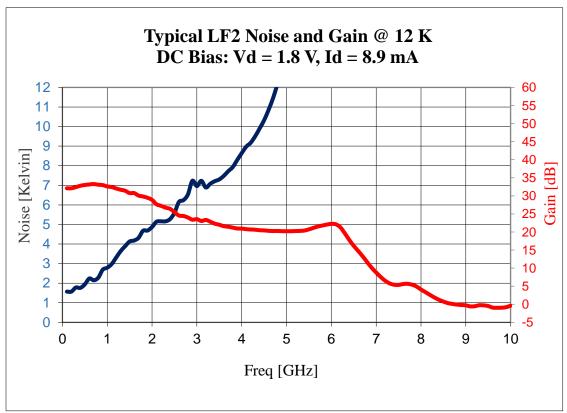
Description	Typical	Minimum	Maximum
RF Frequency		0.01 GHz	1.5 GHz
Gain		$33 \text{ dB} \pm 3 \text{ dB}$	
Noise Temperature	< 4 K	2 K	4 K
IRL (-20log S ₁₁)		< -10 dB	
ORL (-20log S22)		<-10 dB	
DC Voltage	1.8 V	1.1 V	5 V
DC Current	8.9 mA	1.3 mA	44 mA

Electrical Specifications @ 300 K

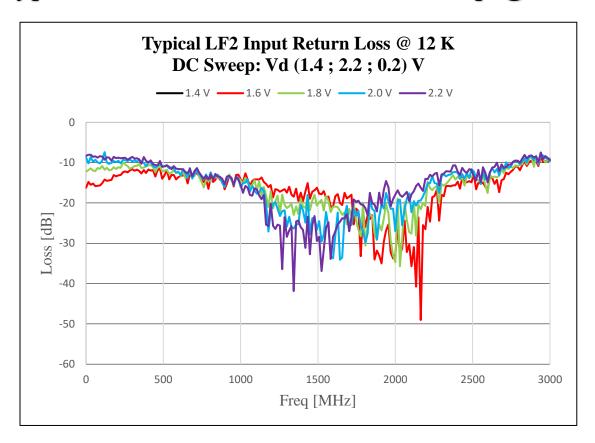
Description	Typical	Minimum	Maximum
RF Frequency		0.01 GHz	1.5 GHz
Gain		25 dB ± 3 dB	
Noise Temperature	< 70 K	45 K	70 K
IRL (-20log S ₁₁)		<-10 dB	
ORL (-20log S22)		<-10 dB	
DC Voltage	1.8 V	1.1 V	5 V
DC Current	10.7 mA	3.7 mA	44 mA

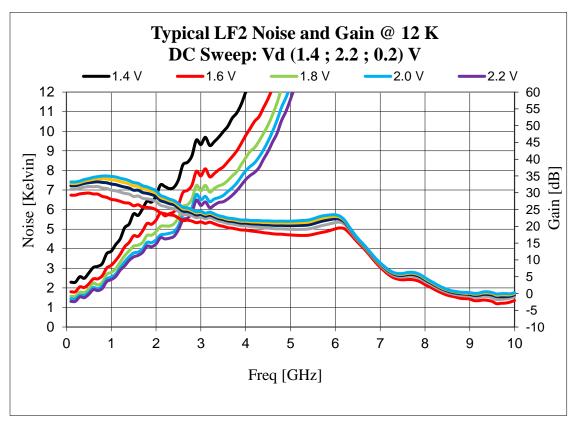
Typical Test Results – Optimum DC Bias @ 12 K



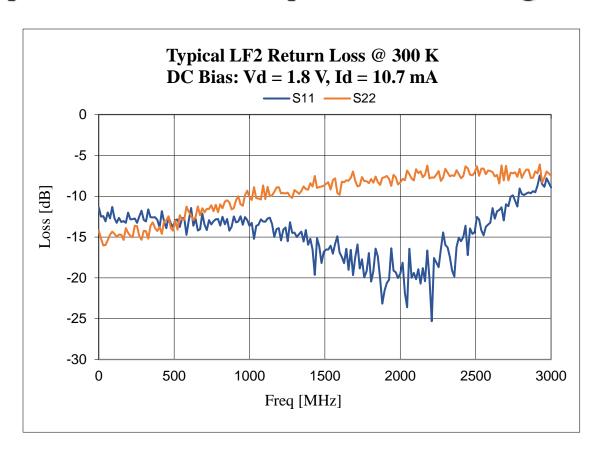


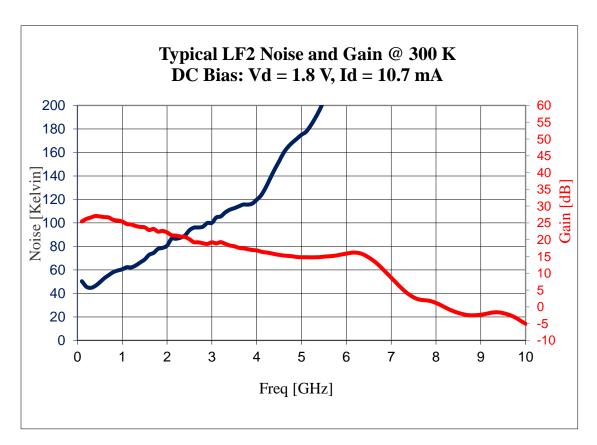
Typical Test Results – DC Bias Sweep @ 12 K



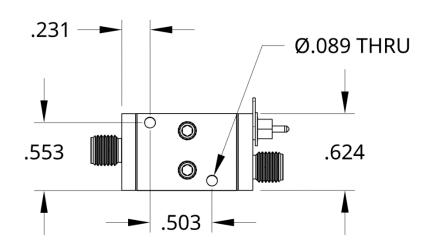


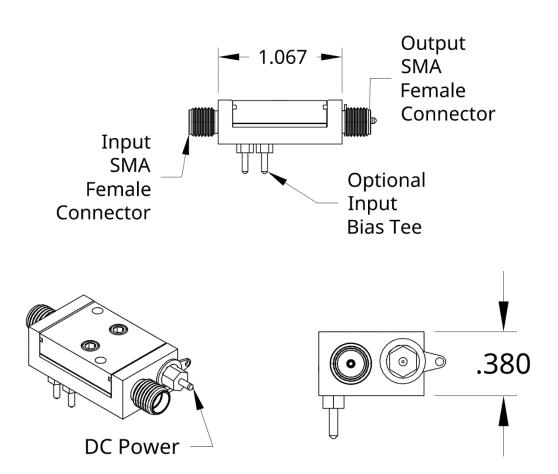
Typical Test Results – Optimum DC Bias @ 300 K





CAD Housing Drawing





*Dimensions are in inches

Optional Input Bias Tee

As an option, the amplifier can be supplied with a DC bias tee for an external device connected to the amplifier input. The bias tee is formed by two (2) resistors connected to the input; as shown in Figure 1. One (1) resistor can be used as a source of current and the other senses the voltage across the external device. Voltages applied to the bias tee have a small effect on amplifier operation. At 12 K, 20 K Ω resistors increase noise by 0.5 K.

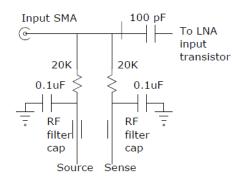
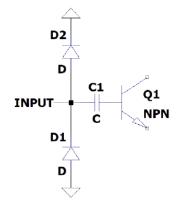


Figure 1. Bias Tee Schematic

To order an amplifier with internal bias resistors, add the resistance to the part #. For instance, CITLF1-20K.

Optional Input Protection Diodes

As an option, the amplifier can be supplied with ESD protection & voltage spike protection at the RF input to the amplifier. There will be a slight degradation of the amplifier performance. Please note that the optional input protection diodes cannot be used if DC voltages are applied to the RF line using input bias tees.



D1 & D2 = Input Protection Diodes

Figure 2. Protection Diodes Schematic

Product Care and Maintenance

- ➤ Use care to not bend (and break) the DC bias pin when tightening the output SMA connector.
- ➤ The amplifier should not be connected to the power supply when connecting the input connector.
- Set the power of Port 1 in your VNA to be less than -45 dB when testing the amplifier. Otherwise, the amplifier may saturate and the data obtained will be incorrect.
- > Do not attempt to open the amplifier.
- Electrostatic discharge may damage the amplifier

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